# VS-VSKDS200/045

**Vishay Semiconductors** 





www.vishay.com

| PRODUCT SUMMARY    |                        |  |  |  |
|--------------------|------------------------|--|--|--|
| I <sub>F(AV)</sub> | 100 A                  |  |  |  |
| V <sub>R</sub>     | 45 V                   |  |  |  |
| Package            | AAP GEN VII (TO-240AA) |  |  |  |
| Circuit            | Two diodes in series   |  |  |  |

## **MECHANICAL DESCRIPTION**

The ADD-A-PAK generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

## FEATURES

- 150 °C T<sub>J</sub> operation
- Low forward voltage drop
- High frequency operation
- Low thermal resistance
- UL pending
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- High surge capability
- Easy mounting on heatsink

### **ELECTRICAL DESCRIPTION**

The VS-VSKDS200/045 Schottky rectifier doubler module has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150 °C junction temperature.

Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

| MAJOR RATINGS AND CHARACTERISTICS |   |                              |    |  |  |  |
|-----------------------------------|---|------------------------------|----|--|--|--|
| SYMBOL                            | CHARACTERISTICS                               | CHARACTERISTICS VALUES UNITS |    |  |  |  |
| I <sub>F(AV)</sub>                | Rectangular waveform                          | 100                          | А  |  |  |  |
| V <sub>RRM</sub>                  |   | 45                           | V  |  |  |  |
| I <sub>FSM</sub>                  | t <sub>p</sub> = 5 μs sine                    | 12 800                       | А  |  |  |  |
| V <sub>F</sub>                    | 100 A <sub>pk</sub> , T <sub>J</sub> = 125 °C | 0.73                         | V  |  |  |  |
| TJ                                | Range   | -55 to +150                  | °C |  |  |  |

| VOLTAGE RATINGS                      |                  |                 |       |  |  |
|--------------------------------------|------------------|-----------------|-------|--|--|
| PARAMETER                            | SYMBOL           | VS-VSKDS200/045 | UNITS |  |  |
| Maximum DC reverse voltage           | V <sub>R</sub>   | 45              | V     |  |  |
| Maximum working peak reverse voltage | V <sub>RWM</sub> | 40              | V     |  |  |



Revision: 17-Jun-14

Document Number: 94966

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

# VS-VSKDS200/045



Vishay Semiconductors

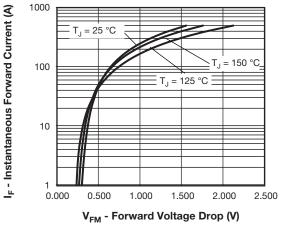
| ABSOLUTE MAXIMUM RATINGS                |                    |   |   |        |       |
|---|--------------------|---|---|--------|-------|
| PARAMETER                               | SYMBOL             | TEST CONDITIONS   |   | VALUES | UNITS |
| Maximum average forward current per leg | I <sub>F(AV)</sub> | $I_{F(AV)}$ 50 % duty cycle at T <sub>C</sub> = 91 °C, rectangular waveform   |   | 100    |       |
| Maximum peak one cycle                  | ESM                | 5 µs sine or 3 µs rect. pulse   | Following any rated load condition and with | 12 800 | А     |
| non-repetitive surge current            |                    | 10 ms sine or 6 ms rect. pulse  | rated $V_{RRM}$ applied                     | 1700   |       |
| Non-repetitive avalanche energy         | E <sub>AS</sub>    | T <sub>J</sub> = 25 °C, I <sub>AS</sub> = 19 A, L = 1 mH  |   | 180    | mJ    |
| Repetitive avalanche current            | I <sub>AR</sub>    | Current decaying linearly to zero in 1 $\mu$ s<br>Frequency limited by T <sub>J</sub> maximum V <sub>A</sub> = 1.5 x V <sub>R</sub> typical |   | 15     | А     |

| ELECTRICAL SPECIFICATIONS       |                  |  |                                 |                            |      |
|---------------------------------|------------------|--|---------------------------------|----------------------------|------|
| PARAMETER                       | SYMBOL           | TEST CO  | TEST CONDITIONS                 |                            |      |
|                                 |                  | 100 A  | T.I = 25 °C                     | 0.67                       | V    |
| Maximum forward voltage drop    | V <sub>FM</sub>  | 200 A  | 1j=25 C                         | 0.92                       |      |
| Maximum forward voltage drop    |                  | 100 A  | T 405.00                        | 0.73                       |      |
|                                 |                  | 200 A  | T <sub>J</sub> = 125 °C         | 1.14                       |      |
| Maximum roverse leakage ourrent | I <sub>RM</sub>  | T <sub>J</sub> = 25 °C   | $V_{\rm B}$ = Rated $V_{\rm B}$ | 10                         | mA   |
| Maximum reverse leakage current |                  | T <sub>J</sub> = 125 °C  | $v_{\rm R} = nateu v_{\rm R}$   | 800                        |      |
| Maximum junction capacitance    | CT               | $V_{R}$ = 5 $V_{DC}$ (test signal range 100 kHz to 1 MHz), 25 °C |                                 | 5200                       | pF   |
| Typical series inductance       | L <sub>S</sub>   | Measured lead to lead 5 mm from package body                     |                                 | 7.0                        | nH   |
| Maximum voltage rate of change  | dV/dt            | Rated V <sub>R</sub> 1   |                                 | 10 000                     | V/µs |
| Maximum RMS insulation voltage  | V <sub>INS</sub> | 50 Hz  |                                 | 3000 (1 min)<br>3600 (1 s) | V    |

| THERMAL - MECHANICAL SPECIFICATIONS                     |             |                                   |  |             |          |  |
|---|-------------|-----------------------------------|--|-------------|----------|--|
| PARAMETER   |             | SYMBOL                            | TEST CONDITIONS  | VALUES      | UNITS    |  |
| Maximum junction and storage temperature range          | )           | T <sub>J</sub> , T <sub>Stg</sub> |  | -55 to +150 | °C       |  |
| Maximum thermal resistance, junction to case per leg    |             | R <sub>thJC</sub>                 | R <sub>thJC</sub> DC operation   |             | °C/W     |  |
| Typical thermal resistance, case to heatsink per module |             | R <sub>thCS</sub>                 |  | 0.1         | 0,10     |  |
| Approximate weight                                      |             |                                   |  | 75          | g        |  |
| Approximate weight                                      |             |                                   |  | 2.7         | oz.      |  |
| Mounting torque ± 10 %                                  | to heatsink |                                   | A mounting compound is recommended and the torque should be rechecked after a period of 3 h to allow for the |             | Nm       |  |
| busbar  |             |                                   | spread of the compound.  | 3           |          |  |
| Case style  |             |                                   | JEDEC®   | TO-240AA co | mpatible |  |

# VS-VSKDS200/045

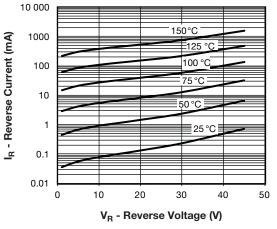
## **Vishay Semiconductors**



www.vishay.com

ISHAY

Fig. 1 - Maximum Forward Voltage Drop Characteristics





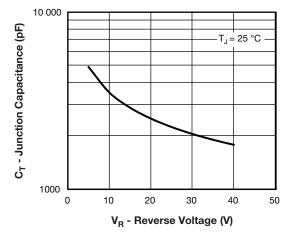


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

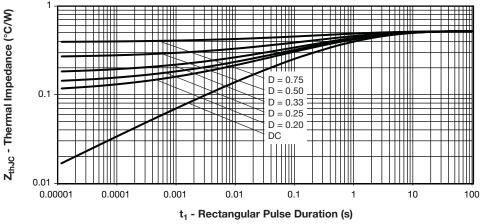
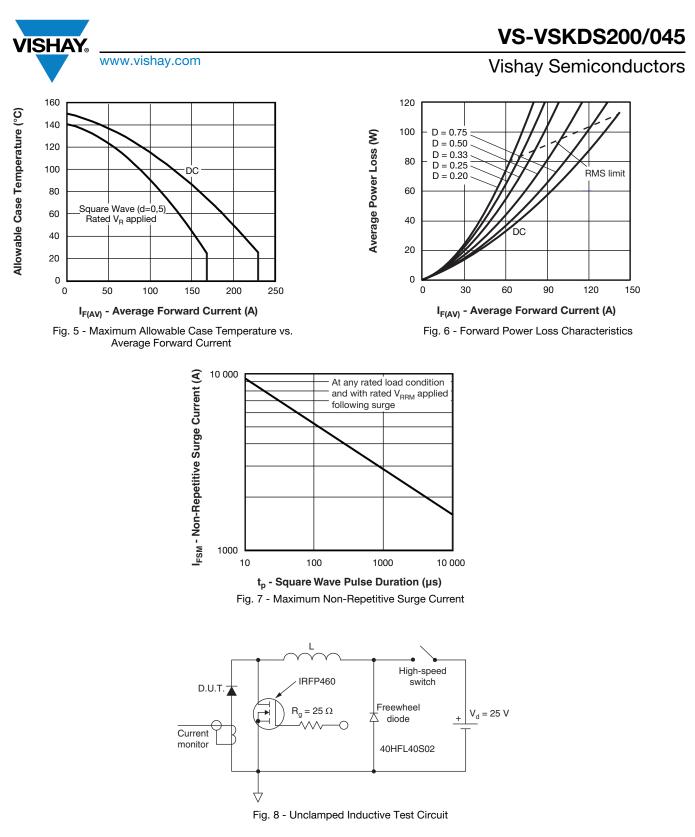


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



#### Note

- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ;
- Pd = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6);
- $Pd_{REV}$  = Inverse power loss =  $V_{R1} \times I_R (1 D)$ ;  $I_R$  at  $V_{R1}$  = 80 % rated  $V_R$

Revision: 17-Jun-14

4

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

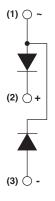
## Vishay Semiconductors



## **ORDERING INFORMATION TABLE**

| Device code | VS-VS                                  | KD                              | S   | 20   | 0                                      | 1                         | 045 |
|-------------|--|---------------------------------|---|--|--|---------------------------|-----|
|             | 1                                      | 2                               | 3   | 4  | 5                                      |                           | 6   |
|             | 1 -<br>2 -<br>3 -<br>4 -<br>5 -<br>6 - | Circ<br>KD<br>S =<br>Ave<br>Pro | hay Sem<br>cuit conf<br>= ADD-,<br>Schottk<br>erage cu<br>duct silio<br>tage rati | iguratior<br>A-PAK -<br>y diode<br>rrent rat<br>con iden | n:<br>2 diode<br>ing (20<br>itificatio | es in sei<br>= 200 A<br>n |     |

## **CIRCUIT CONFIGURATION**



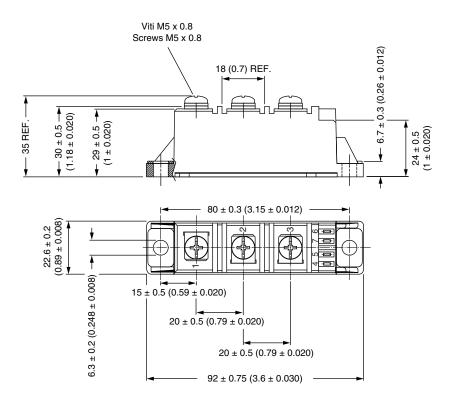
| LINKS TO RELATED DOCUMENTS |                          |  |  |  |
|----------------------------|--------------------------|--|--|--|
| Dimensions                 | www.vishay.com/doc?95369 |  |  |  |

**Vishay Semiconductors** 



## **ADD-A-PAK Generation VII - Diode**

## **DIMENSIONS** in millimeters (inches)





Vishay

# Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.